

# SEMiX404GB12Vs



SEMiX® 4s

## SEMiX404GB12Vs

### Features

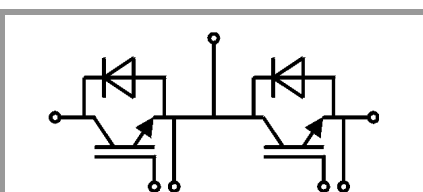
- Homogeneous Si
- $V_{CE(sat)}$  with positive temperature coefficient
- High short circuit capability
- UL recognised file no. E63532

### Typical Applications\*

- AC inverter drives
- UPS
- Electronic Welding

### Remarks

- Case temperature limited to  $T_C=125^\circ\text{C}$  max.
- Product reliability results are valid for  $T_j=150^\circ\text{C}$
- Dynamic values apply to the following combination of resistors:  
 $R_{Gon,main} = 1,8 \Omega$   
 $R_{Goff,main} = 1,8 \Omega$   
 $R_{G,X} = 2,2 \Omega$   
 $R_{E,X} = 0,5 \Omega$



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Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
<b>IGBT</b>				
$V_{CES}$		1200	V	
$I_C$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	596	A
		$T_c = 80^\circ\text{C}$	455	A
$I_{Cnom}$		400	A	
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$	1200	A	
$V_{GES}$		-20 ... 20	V	
$t_{psc}$	$V_{CC} = 600\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 125^\circ\text{C}$	10	$\mu\text{s}$
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Inverse diode</b>				
$I_F$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	440	A
		$T_c = 80^\circ\text{C}$	329	A
$I_{Fnom}$		400	A	
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$	1200	A	
$I_{FSM}$	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	1980	A	
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Module</b>				
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$	600	A	
$T_{stg}$		-40 ... 125	$^\circ\text{C}$	
$V_{isol}$	AC sinus 50Hz, $t = 1\text{ min}$	4000	V	

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
<b>IGBT</b>					
$V_{CE(sat)}$	$I_C = 400\text{ A}$ $V_{GE} = 15\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$	1.75	2.2	V
		$T_j = 150^\circ\text{C}$	2.2	2.5	V
$V_{CE0}$		$T_j = 25^\circ\text{C}$	0.94	1.04	V
		$T_j = 150^\circ\text{C}$	0.88	0.98	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	2.0	2.9	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	3.3	3.8	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C = 16\text{ mA}$	5.5	6	6.5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	$\text{mA}$
		$T_j = 150^\circ\text{C}$			$\text{mA}$
$C_{ies}$	$V_{CE} = 25\text{ V}$		24.0		nF
$C_{oes}$	$V_{GE} = 0\text{ V}$		2.36		nF
$C_{res}$			2.36		nF
$Q_G$	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		4400		nC
$R_{Gint}$	$T_j = 25^\circ\text{C}$		1.88		$\Omega$
$t_{d(on)}$	$V_{CC} = 600\text{ V}$ $I_C = 400\text{ A}$	$T_j = 150^\circ\text{C}$	517		ns
$t_r$	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$	94		ns
$E_{on}$	$R_{Gon} = 2.5\ \Omega$	$T_j = 150^\circ\text{C}$	39.1		mJ
$t_{d(off)}$	$R_{Goff} = 2.5\ \Omega$	$T_j = 150^\circ\text{C}$	788		ns
$t_f$	$di/dt_{on} = 4200\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	102		ns
$E_{off}$	$di/dt_{off} = 3600\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	52.3		mJ
	$du/dt_{off} = 6800\text{ V}/\mu\text{s}$				
$R_{th(j-c)}$	per IGBT		0.075		K/W

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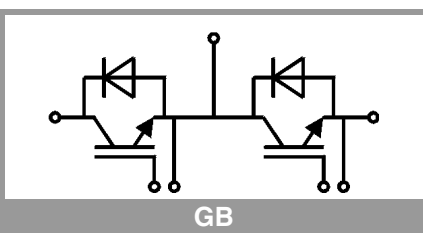
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Inverse diode</b>						
$V_F = V_{EC}$	$I_F = 400 \text{ A}$ $V_{GE} = 0 \text{ V}$ chip	$T_j = 25^\circ\text{C}$		2.2	2.52	V
		$T_j = 150^\circ\text{C}$		2.1	2.5	V
$V_{F0}$		$T_j = 25^\circ\text{C}$	1.1	1.3	1.5	V
		$T_j = 150^\circ\text{C}$	0.7	0.9	1.1	V
$r_F$		$T_j = 25^\circ\text{C}$	2.0	2.3	2.5	m $\Omega$
		$T_j = 150^\circ\text{C}$	2.6	3.1	3.4	m $\Omega$
$I_{RRM}$	$I_F = 400 \text{ A}$ $di/dt_{off} = 4100 \text{ A}/\mu\text{s}$ $V_{GE} = -15 \text{ V}$ $V_{CC} = 600 \text{ V}$	$T_j = 150^\circ\text{C}$		309		A
$Q_{rr}$		$T_j = 150^\circ\text{C}$		73		$\mu\text{C}$
$E_{rr}$		$T_j = 150^\circ\text{C}$			34.3	
$R_{th(j-c)}$	per diode				0.14	K/W
<b>Module</b>						
$L_{CE}$				22		nH
$R_{CC'+EE'}$	res., terminal-chip	$T_C = 25^\circ\text{C}$		0.7		m $\Omega$
		$T_C = 125^\circ\text{C}$		1		m $\Omega$
$R_{th(c-s)}$	per module			0.03		K/W
$M_s$	to heat sink (M5)		3		5	Nm
$M_t$		to terminals (M6)	2.5		5	Nm
						Nm
$w$					400	g
<b>Temperatur Sensor</b>						
$R_{100}$	$T_C=100^\circ\text{C}$ ( $R_{25}=5 \text{ k}\Omega$ )			$493 \pm 5\%$		$\Omega$
$B_{100/125}$	$R(T)=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$ ; $T[\text{K}]$ ;			$3550 \pm 2\%$		K



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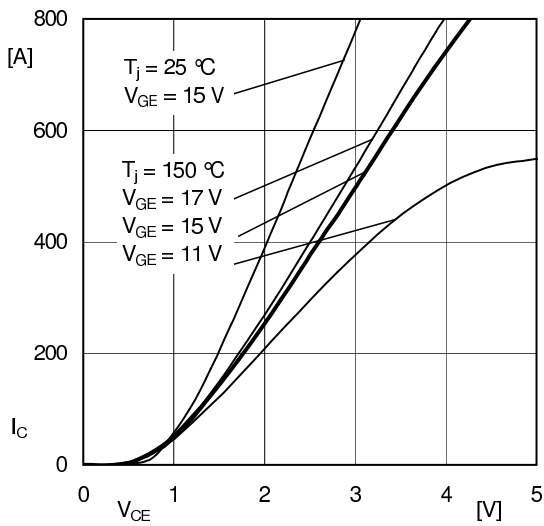


Fig. 1: Typ. output characteristic, inclusive  $R_{CC+EE}$

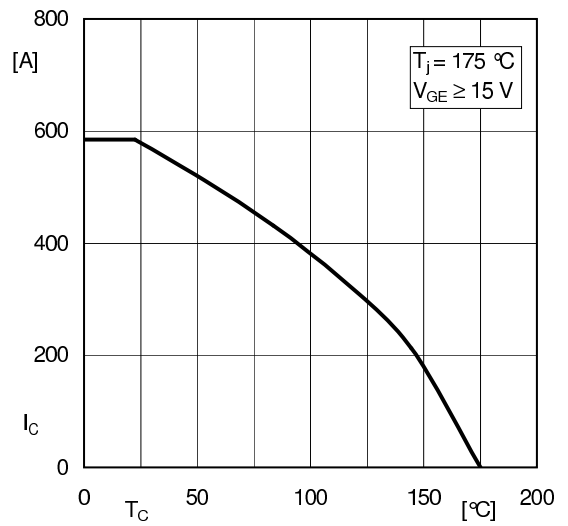


Fig. 2: Rated current vs. temperature  $I_C = f(T_C)$

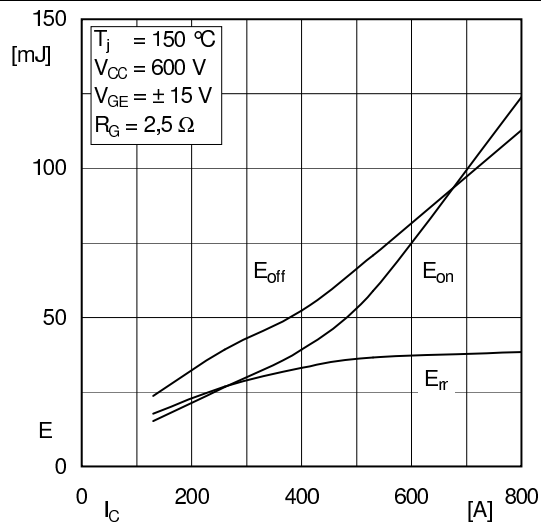


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

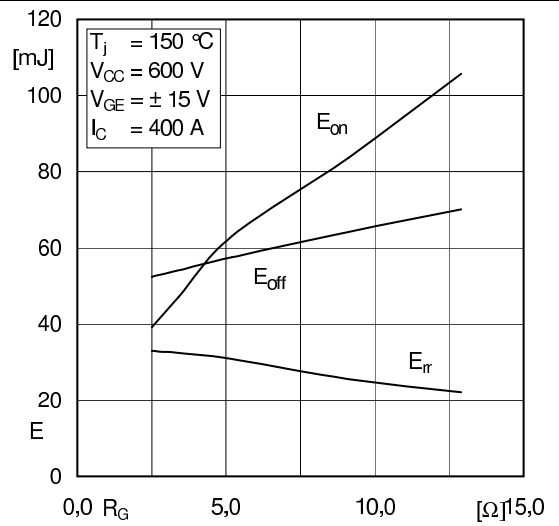


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

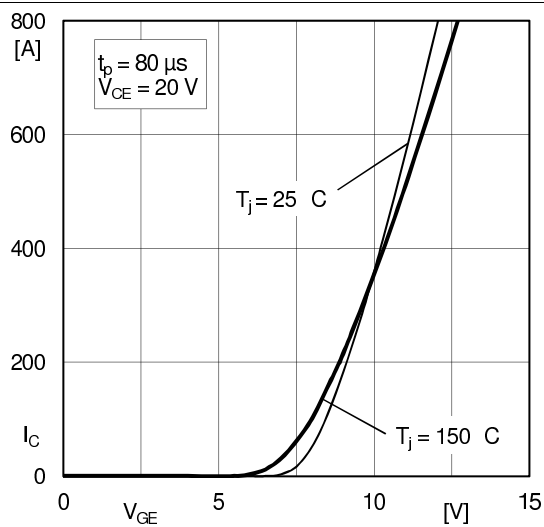


Fig. 5: Typ. transfer characteristic

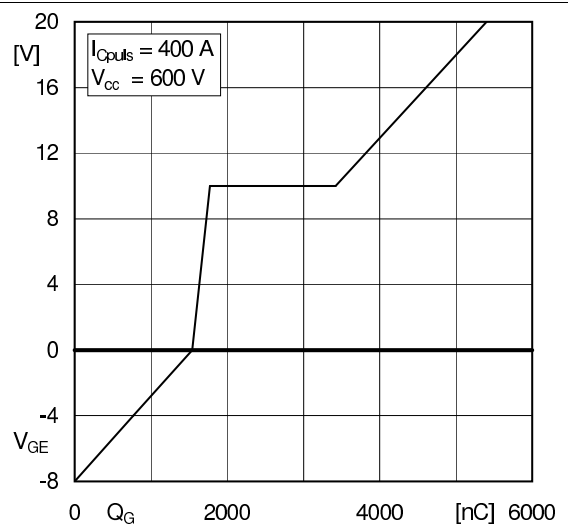
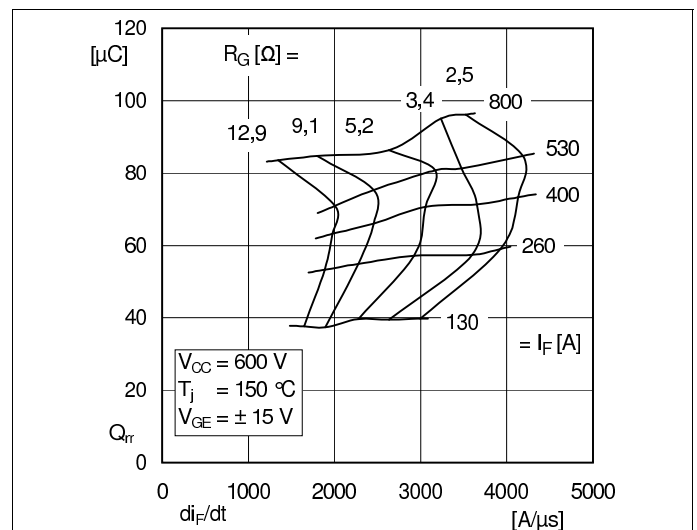
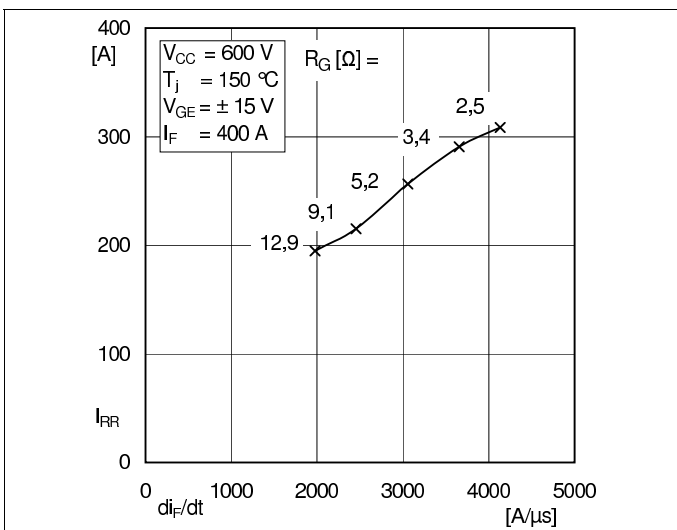
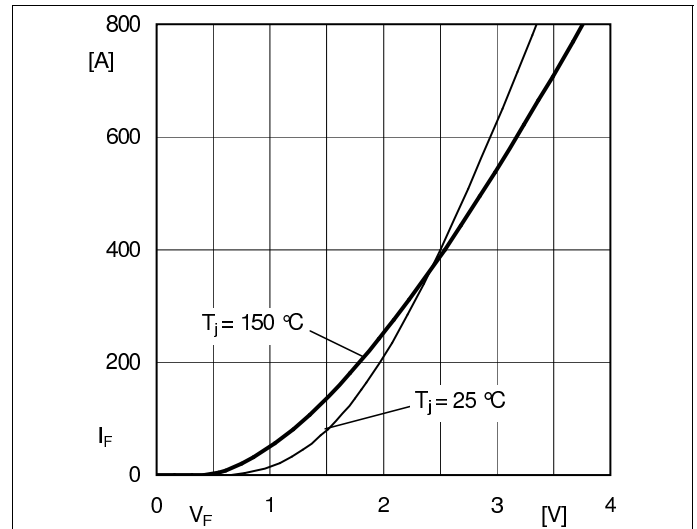
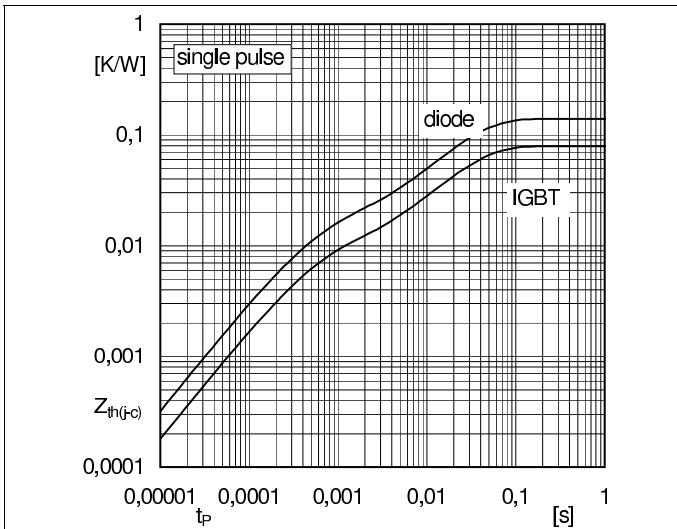
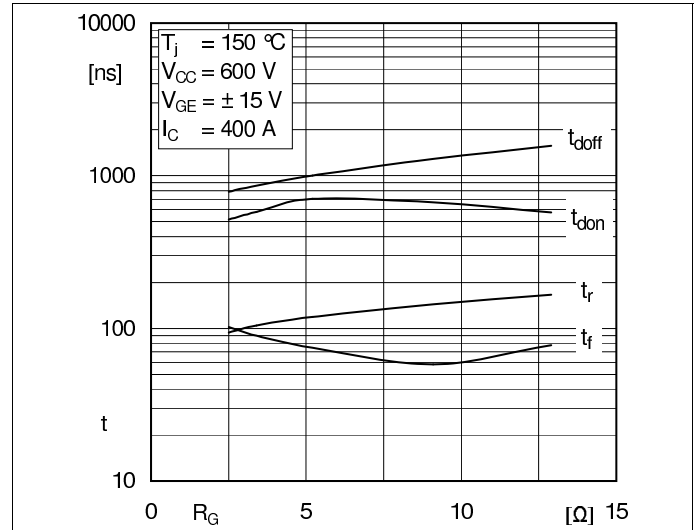
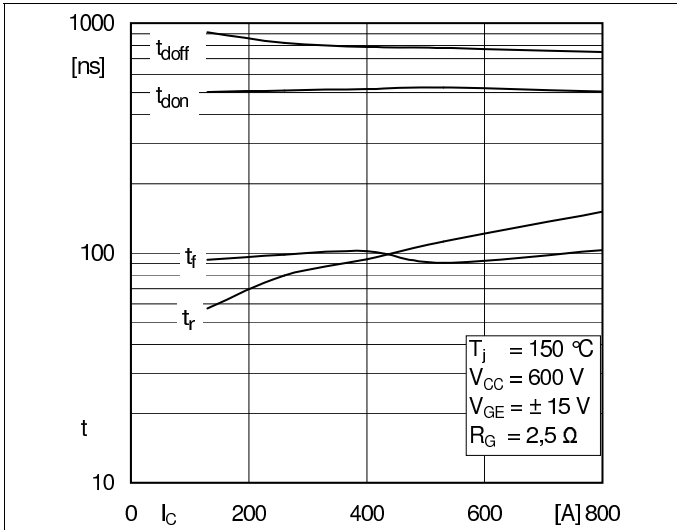


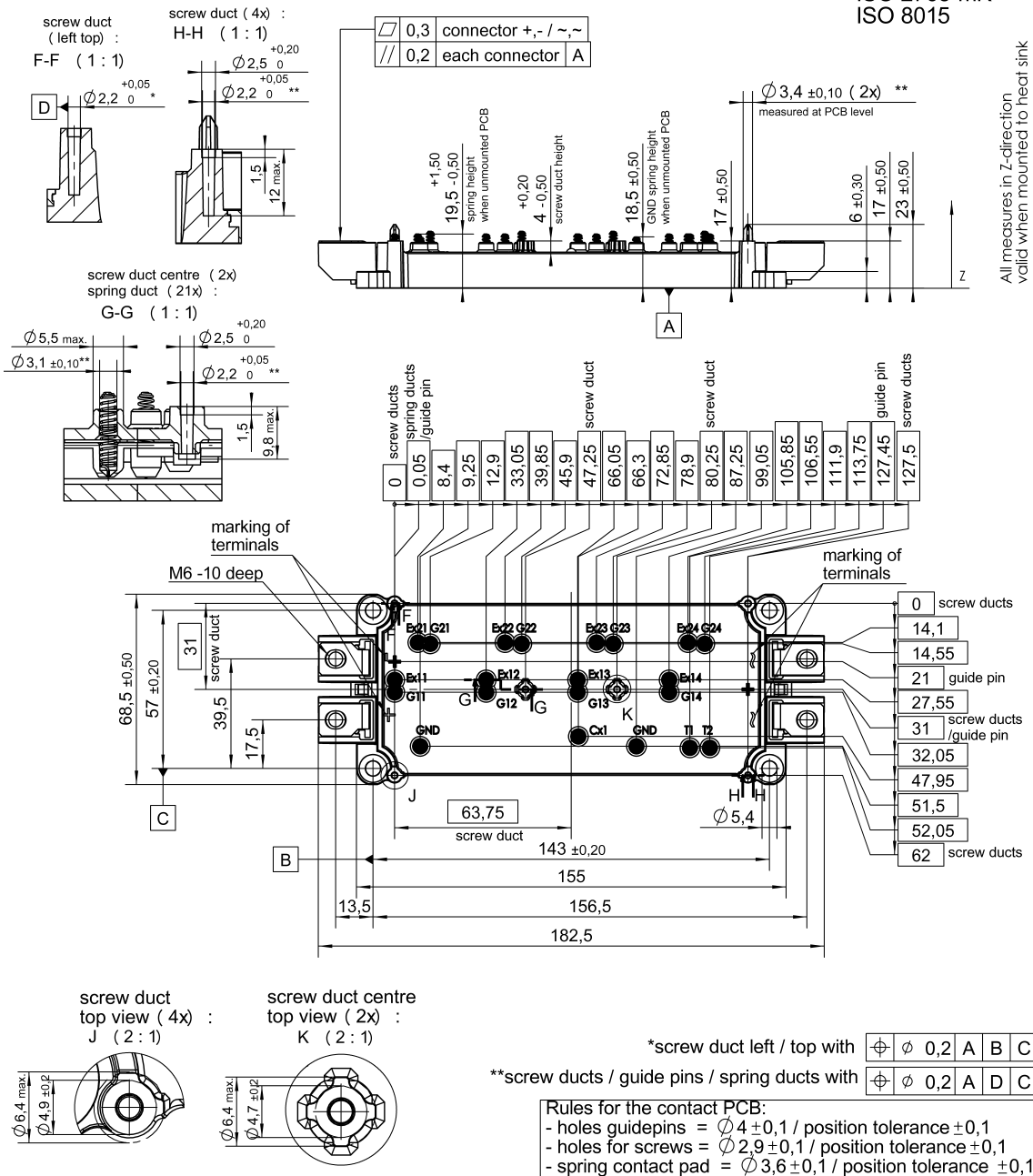
Fig. 6: Typ. gate charge characteristic



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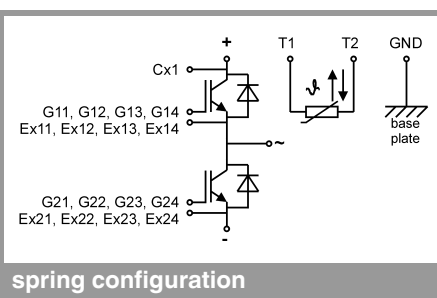
Case: SEMiX 4s

general tolerance:  
ISO 2768-mK  
ISO 8015



All measures in Z-direction valid when mounted to heat sink

SEMiX 4s



spring configuration

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.